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STP24NF10;ST;TO220;tranzystor; N-CHANNEL;26A;100V;85W;0.055R



Dane techniczne:

Nazwa: STP24NF10

Typ tranzystora: unipolarny

Kierunek przewodnictwa: N-MOSFET

Prąd kolektora: 26A

Napięcie kolektor-emiter: 100V

Moc: 85W

Montaż: przewlekany(THT)

Obudowa: TO220

Producent: ST

www.podzespoly-elektroniczne.pl

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STB24NF10 STP24NF10

N-channel 100V - 0.0055Ω - 26A - TO-220 - D²PAK
Low gate charge STripFET™ II Power MOSFET

General features

Type	V _{DSS}	R _{DS(on)}	I _D
STB24NF10	100V	<0.060Ω	26A
STP24NF10	100V	<0.060Ω	26A

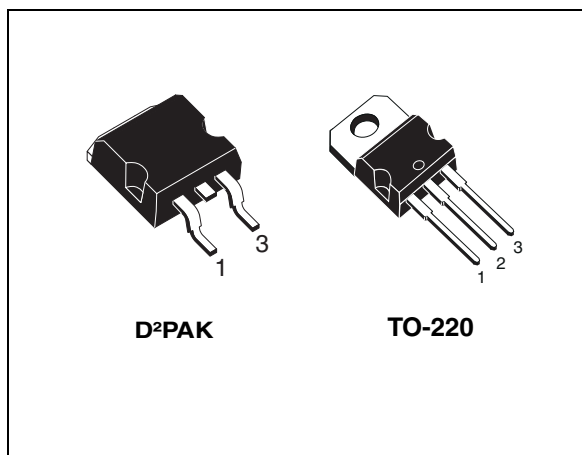
- Exceptional dv/dt capability
- 100% avalanche tested
- Application oriented characterization

Description

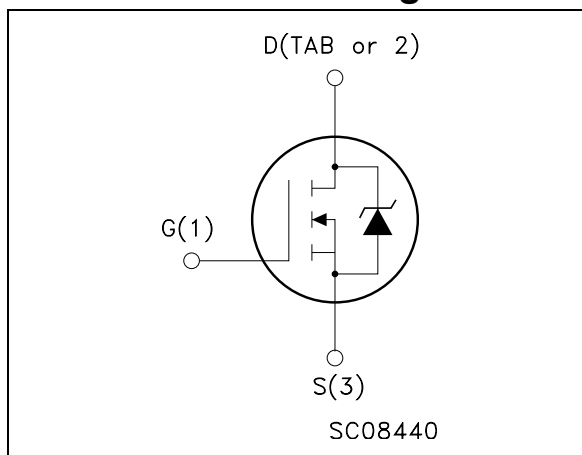
This Power MOSFET series realized with STMicroelectronics unique STripFET™ process has specifically been designed to minimize the on-resistance. It is therefore suitable as primary switch in advanced high-efficiency, high-frequency isolated DC-DC converters for Telecom and Computer application. It is also intended for any applications with low gate drive requirements.

Applications

- Switching application



Internal schematic diagram



Order codes

Part number	Marking	Package	Packaging
STP24NF10	P24NF10	TO-220	Tube
STB24NF10	B24NF10	D ² PAK	Tape & reel

Contents

1	Electrical ratings	3
2	Electrical characteristics	4
2.1	Electrical characteristics (curves)	6
3	Test circuit	8
4	Package mechanical data	9
5	Packaging mechanical data	12
6	Revision history	13

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	100	V
V_{DGR}	Drain-gate voltage ($R_{GS}=20k\Omega$)	100	V
V_{GS}	Gate-source voltage	± 20	V
I_D	Drain current (continuous) at $T_C = 25^\circ\text{C}$	26	A
I_D	Drain current (continuous) at $T_C=100^\circ\text{C}$	18	A
$I_{DM}^{(1)}$	Drain current (pulsed)	104	A
P_{TOT}	Total dissipation at $T_C = 25^\circ\text{C}$	85	W
	Derating factor	0.57	W/°C
$dv/dt^{(2)}$	Peak diode recovery voltage slope	9	V/ns
$E_{AS}^{(3)}$	Single pulse avalanche energy	220	mJ
T_J	Operating junction temperature	-55 to 175	°C
T_{stg}	Storage temperature		

1. Pulse width limited by safe operating area.
2. $I_{SD} \leq 24\text{A}$, $di/dt \leq 300\text{A}/\mu\text{s}$, $V_{DD}=80\%V_{(BR)DSS}$
3. Starting $T_j = 25^\circ\text{C}$, $I_D=12\text{A}$, $V_{DD}=30\text{V}$

Table 2. Thermal resistance

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case Max	1.76	°C/W
$R_{thj-amb}$	Thermal resistance junction-ambient Max	62.5	°C/W
T_j	Maximum lead temperature for soldering purpose	300	°C

2 Electrical characteristics

($T_{CASE}=25^{\circ}C$ unless otherwise specified)

Table 3. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\mu A, V_{GS} = 0$	100			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating},$ $V_{DS} = \text{Max rating} @ 125^{\circ}C$			1 10	μA μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20V$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	2	3	4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10V, I_D = 12A$		0.055	0.060	Ω

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 15V, I_D = 12A$		10		S
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25V, f = 1 \text{ MHz}, V_{GS} = 0$		870 125 50		pF pF pF
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 80V, I_D = 24A$ $V_{GS} = 10V$ (see Figure 7)		30 6 10	41	nC nC nC

1. Pulsed: pulse duration=300 μs , duty cycle 1.5%

Table 5. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Turn-on delay time Rise time Turn-off delay time Fall time	$V_{DD} = 50V, I_D = 12A,$ $R_G = 4.7\Omega, V_{GS} = 10V$ (see Figure 12)		60 15 50 20		ns ns ns ns

Table 6. Source drain diode

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
I_{SD}	Source-drain current				26	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				104	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD}=24A, V_{GS}=0$			1.5	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD}=24A,$ $di/dt = 100A/\mu s,$ $V_{DD}=30V, T_j=150^\circ C$ (see Figure 14)		100 375 7.5		ns nC A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration=300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

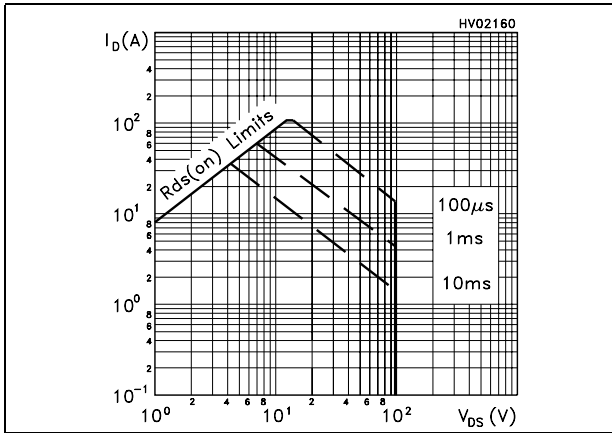


Figure 2. Thermal impedance

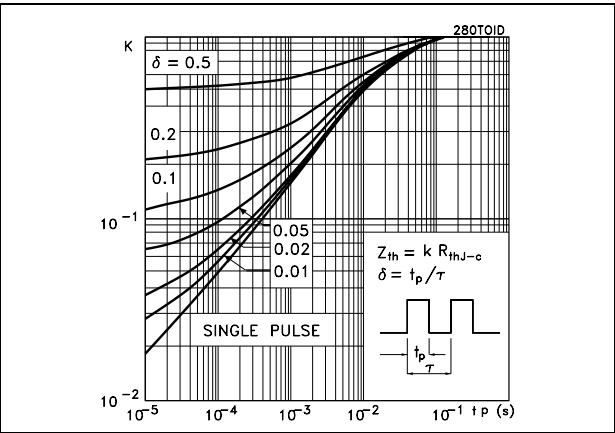


Figure 3. Output characteristics

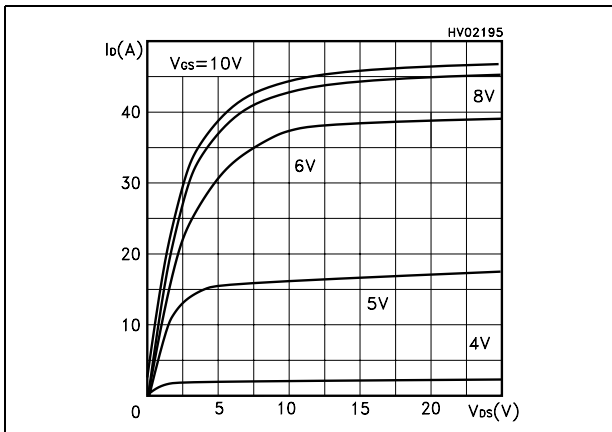


Figure 4. Transfer characteristics

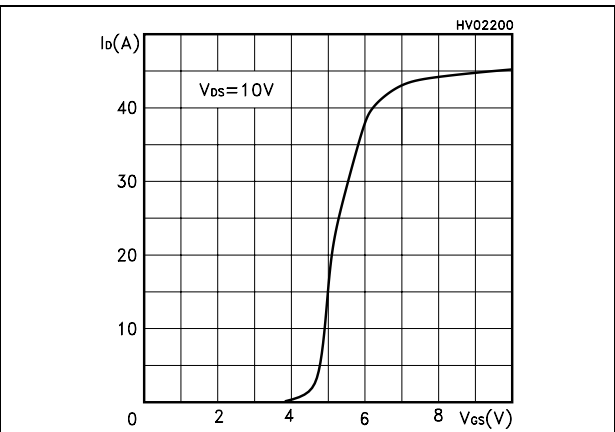


Figure 5. Transconductance

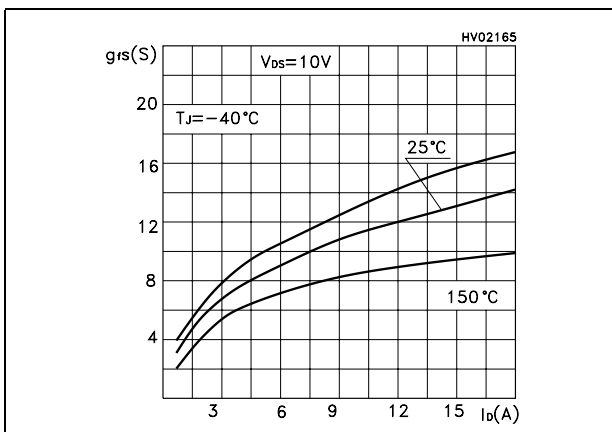


Figure 6. Static drain-source on resistance

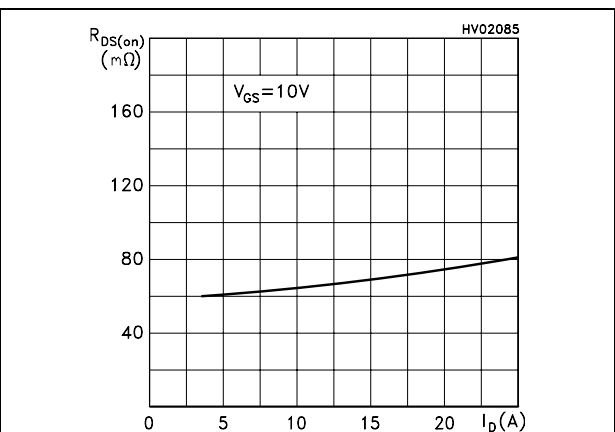


Figure 7. Gate charge vs gate-source voltage Figure 8. Capacitance variations

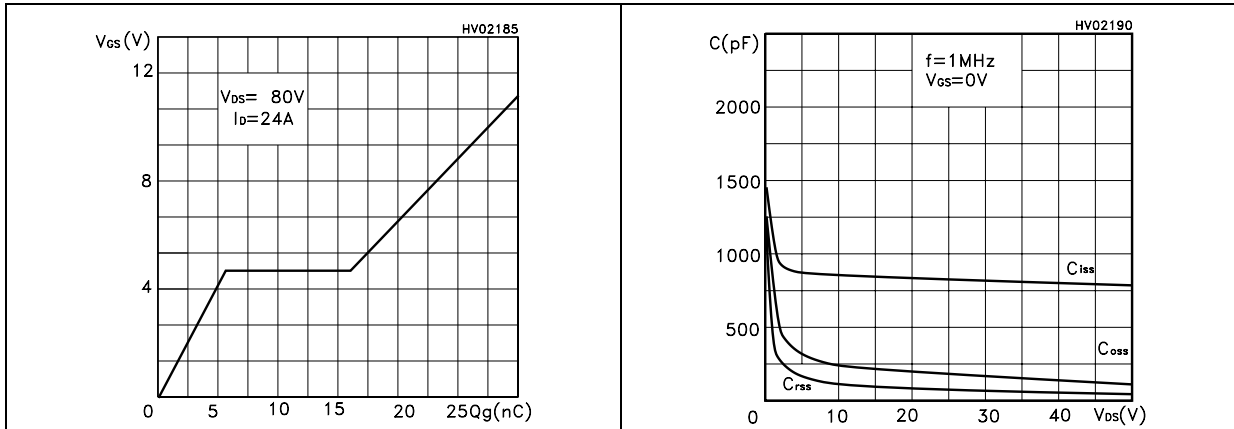


Figure 9. Normalized gate threshold voltage vs temperature Figure 10. Normalized on resistance vs temperature

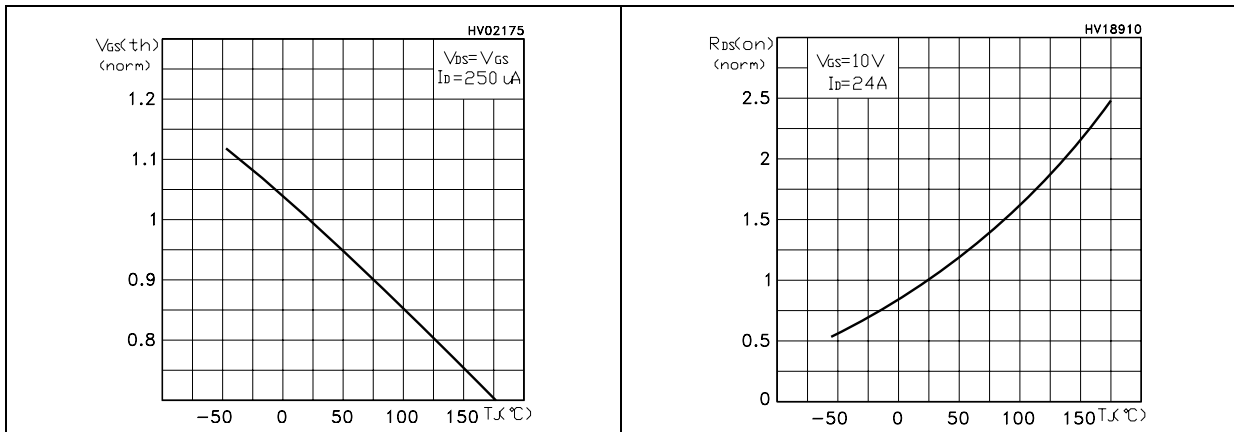
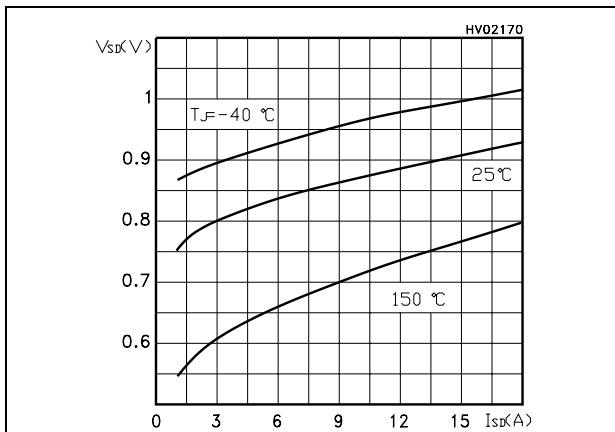


Figure 11. Source-drain diode forward characteristics



3 Test circuit

Figure 12. Switching times test circuit for resistive load

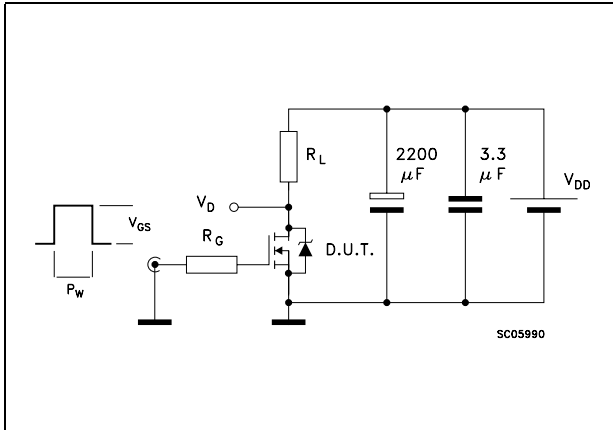


Figure 13. Gate charge test circuit

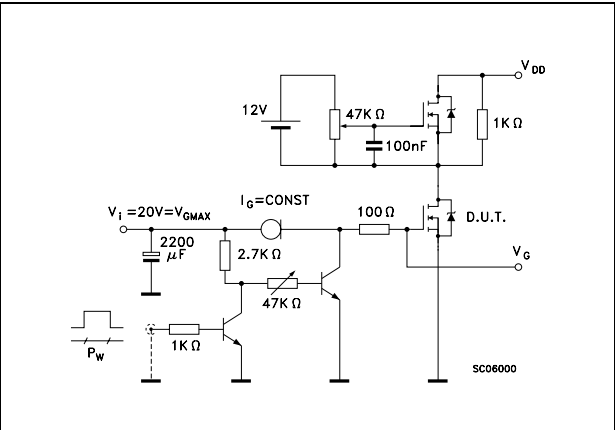


Figure 14. Test circuit for inductive load switching and diode recovery times



Figure 15. Unclamped inductive load test circuit



Figure 16. Unclamped inductive waveform



Figure 17. Switching time waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

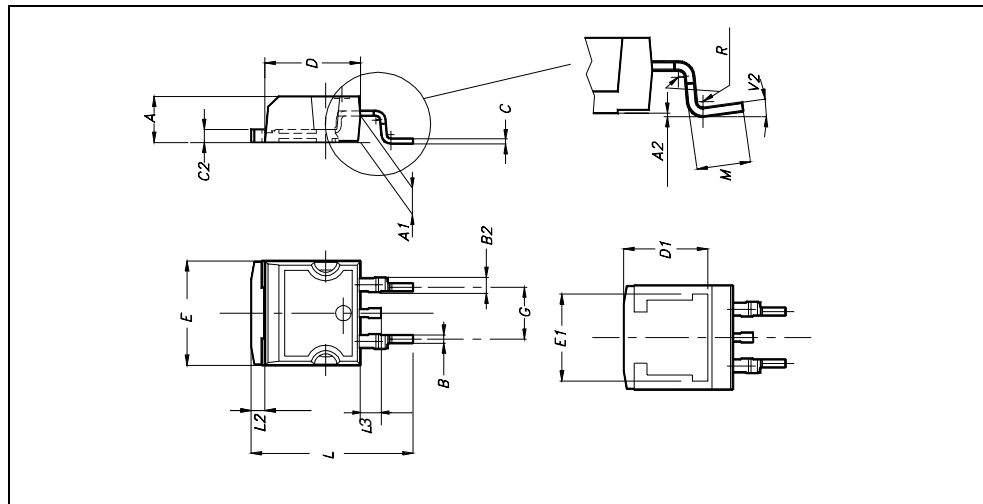
TO-220 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



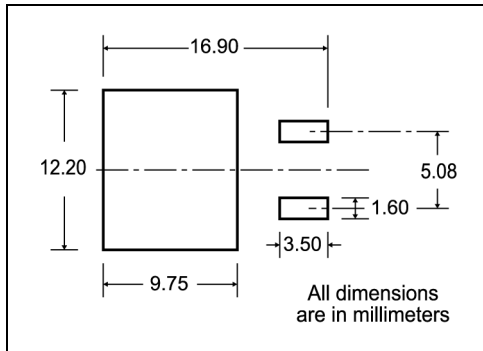
D²PAK MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		4°			



5 Packaging mechanical data

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT

40 mm min. Access hole at slot location

Full radius

Tape slot in core for tape start 2.5mm min. width

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956

REEL MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

10 pitches cumulative tolerance on tape +/- 0.2 mm

Center line of cavity

User Direction of Feed

TRL

FEED DIRECTION

Bending radius R min.

* on sales type

6 Revision history

Table 7. Revision history

Date	Revision	Changes
09-Sep-2004	6	Complete version
09-Aug-2006	7	New template, no content change

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